

Switching Diode

Product lineup

Category	Application	V _{RM} (V)	Surface mounting type										
			1208 size	1608 size		2012 size				2916 size			
VMD3	EMD2 (SOD-523)	EMD3 (SOT-416)	UMD2 (SOD-323)	UMD3 (SOT-323)	UMD4 (SOT-343)	UMD5 (SOT-353)	UMD6 (SOT-363)	SMD3 (SOT-346)	SMD5 (SC-74A)	SMD6 (SOT-457)			
Switching diode	High-speed	20	DA221M		DA221		DA204U				DA204K		
		80~90	DAN222M DAP222M	1SS400	DAN222 DAP222	1SS355	DAN202U DAP202U DAN217U DA228U	DA227	UMN1N UMP1N	UMN11N UMP11N UMR12N	DAN202K DAP202K DAN217 DA228K	FMN1 FMP1	IMN10 IMN11 IMP11
	Low reak	40				1SS380							

Surface mounting type

Application	Part no.		Absolute maximum ratings (Ta=25°C) ※1					Electrical characteristics (Ta=25°C) ※1						Package	Equivalent circuit diagram	
			V _{RM} (V)	V _R (V)	I _{FM} (mA)	I _O (mA)	I _{surge} (mA)	V _F (V)Max.	I _R (μA)Max.	t _{rr} (ns)Max.						
	Part no.	Taping code					I _F (mA)	V _R (V)	V _R (V)	I _F (mA)						
High-Speed	1SS400	TE61	90	80	225	100	500(1s)	1.2	100	0.1	80	4	6	10	EMD2	
	1SS355	TE-17	90	80	225	100	500(1s)	1.2	100	0.1	80	4	6	10	UMD2	
	NEW DAN222M	T2L	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	VMD3	
	DAN222	TL	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	EMD3	
	DAN202U	T106	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	UMD3	
	DAN202K	T146	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	SMD3	
	NEW DAP222M	T2L	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	VMD3	
	DAP222	TL	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	EMD3	
	DAP202U	T106	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	UMD3	
	DAP202K	T146	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	SMD3	
	NEW DA221M	T2L	20	20	200	100	300(1μs)	1.0	10	0.1	15	—	—	—	VMD3	
	DA221	TL	20	20	200	100	300(1μs)	1.0	10	0.1	15	—	—	—	EMD3	
	DA204U	T106	20	20	200	100	300(1μs)	1.0	10	0.1	15	—	—	—	UMD3	
	DAN217U	T106	80	80	300	100	4000(1μs)	1.2	100	0.2	70	4	6	5	UMD3	
	DA228U	T106	80	80	200	100	300(1μs)	1.2	100	0.1	80	—	—	—	UMD3	
	DAN217	T146	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	SMD3	
	DA228K	T146	80	80	200	100	300(1μs)	1.2	100	0.1	80	—	—	—	SMD3	
	DA204K	T146	20	20	200	100	300(1μs)	1.0	10	0.1	15	—	—	—	SMD3	
	UMN1N	TR	80	80	80	25	250(1μs)	0.9	5	0.1	70	4	6	5	UMD5	
	FMN1	T148	80	80	80	25	250(1μs)	0.9	5	0.1	70	4	6	5	SMD5	
	UMP1N	TR	80	80	80	25	250(1μs)	0.9	5	0.1	70	4	6	5	UMD5	
	FMP1	T148	80	80	80	25	250(1μs)	0.9	5	0.1	70	4	6	5	SMD5	
	UMN11N	TN	80	80	300	100	4000(1μs)	0.9	100	0.1	70	4	6	5	UMD6	
	IMN11	T110	80	80	300	100	4000(1μs)	0.9	100	0.1	70	4	6	5	SMD6	
UMP11N	TN	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	UMD6		
IMP11	T110	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	SMD6		
UMR12N	TN	80	80	200	100	300(1μs)	1.2	100	0.1	80	—	—	—	UMD6		
DA227	TL	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	UMD4		
IMN10	T108	80	80	300	100	4000(1μs)	1.2	100	0.1	70	4	6	5	SMD6		
Low reak	1SS380	TE-17	40	35	225	100	400(1s)	1.2	100	0.01	20	—	—	—	UMD2	

Note : ※1Value/element.

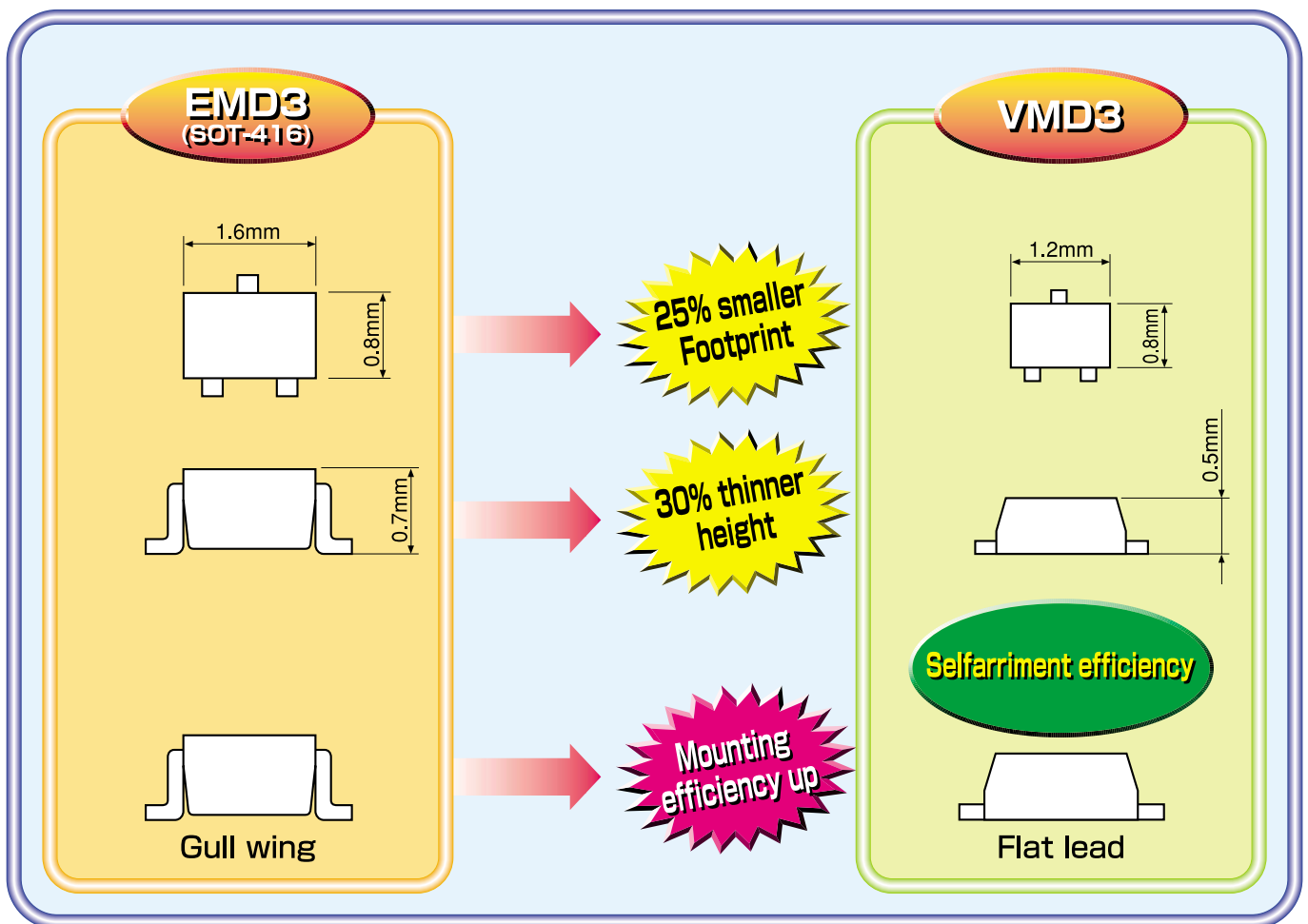
Super small switching diode

Application

- Cellular Phones
- Digital camera
- Digital video camera
- PC, PDA

Merit

1. 25% smaller Footprint
2. 30% thinner height
3. Mounting efficiency up (soldering operation)



Silicon diode (Epitaxial Planer Type)

DAN222M

APPLICATION

High speed switching

Mass per piece

1.3mg/pcs

Absolute maximum ratings (Ta=25°C)

Characteristic	Symbol	Limits
Reverse voltage (repetitive peak)	V _{RM}	80V
Reverse voltage (DC)	V _R	80V
Average rectified forward current	I _O	100mA
Peak forward current	I _{FM}	300mA
Surge current (1 μsec)	I _{surge}	4A
Power dissipation	P _d	150mW / Total ^{※1}
Junction temperature	T _j	150°C
Storage temperature	T _{stg}	-55~150°C
Rated frequency	f	100MHz

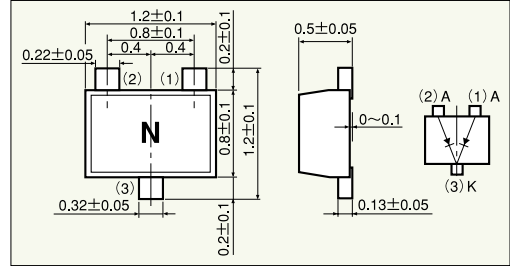
※1 Pd=120mW when only 1 circuit is operating. CONDITION=Each terminal mounted on a recommended land pattern.

ELECTRICAL CHARACTERISTIC (Ta=25°C)

Characteristic	Symbol	Test condition	Max	Unit
Forward voltage	V _F	I _F =100mA	1.2	V
Reverse current	I _R	V _R =70V	0.1	μA
Capacitance between terminal	C _t	V _R =6V f=1.0MHz	3.5	pF
Reverse recovery time	t _{rr}	V _R =6V I _F =5mA R _L =50Ω (See figure1)	4.0	ns

Note : ※1 Value/element.

DIMENSION (UNIT:mm)



Silicon diode (Epitaxial Planer Type)

DAP222M

APPLICATION

High speed switching

Mass per piece

1.3mg/pcs

Absolute maximum ratings (Ta=25°C)

Characteristic	Symbol	Limits
Reverse voltage (repetitive peak)	V _{RM}	80V
Reverse voltage (DC)	V _R	80V
Average rectified forward current	I _O	100mA
Peak forward current	I _{FM}	300mA
Surge current (1 μsec)	I _{surge}	4A
Power dissipation	P _d	150mW / Total ^{※1}
Junction temperature	T _j	150°C
Storage temperature	T _{stg}	-55~150°C
Rated frequency	f	100MHz

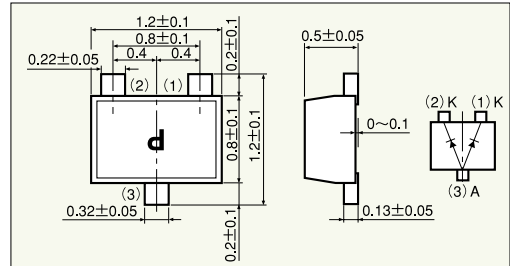
※1 Pd=120mW when only 1 circuit is operating. CONDITION=Each terminal mounted on a recommended land pattern.

ELECTRICAL CHARACTERISTIC (Ta=25°C)

Characteristic	Symbol	Test condition	Max	Unit
Forward voltage	V _F	I _F =100mA	1.2	V
Reverse current	I _R	V _R =70V	0.1	μA
Capacitance between terminal	C _t	V _R =6V f=1.0MHz	3.5	pF
Reverse recovery time	t _{rr}	V _R =6V I _F =5mA R _L =50Ω (See figure1)	4.0	ns

Note : ※1 Value/element.

DIMENSION (UNIT:mm)



Silicon diode (Epitaxial Planer Type)

DA221M

APPLICATION

Bias, Rectifier

Mass per piece

1.3mg/pcs

Absolute maximum ratings (Ta=25°C)

Characteristic	Symbol	Limits
Reverse voltage (repetitive peak)	V _{RM}	20V
Reverse voltage (DC)	V _R	20V
Average rectified forward current	I _O	100mA
Peak forward current	I _{FM}	200mA
Surge current (1 μsec)	I _{surge}	300mA
Power dissipation	P _d	150mW / Total ^{※1}
Junction temperature	T _j	150°C
Storage temperature	T _{stg}	-55~150°C
Rated frequency	f	100MHz

※1 Pd=120mW when only 1 circuit is operating. CONDITION=Each terminal mounted on a recommended land pattern.

ELECTRICAL CHARACTERISTIC (Ta=25°C)

Characteristic	Symbol	Test condition	Max	Unit
Forward voltage	V _F	I _F =10mA	1.0	V
Reverse current	I _R	V _R =15V	0.1	μA
Capacitance between terminal	C _t	V _R =6V f=1.0MHz	4.0	pF

V_F, I_R : Between no.1 pin and no.3pin.
Between no.2pin and no.3pin.
C_t : Between no.1 pin and no.2pin.

DIMENSION (UNIT:mm)

